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#### **60V DUAL N-CHANNEL 175°C MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
	50mΩ @ V <sub>GS</sub> = 10V	16.7A
60V	65mΩ @ V <sub>GS</sub> = 4.5V	14.6A

### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>G</sub> Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

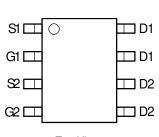
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.076 grams (Approximate)

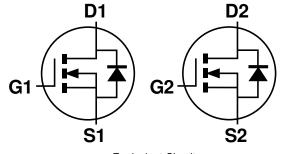


Top View



SO-8

Top View Pin Configuration



**Equivalent Circuit** 

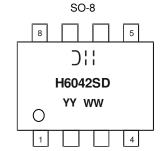
### **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMNH6042SSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### Marking Information



);; = Manufacturer's Marking H6042SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 - 53)



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	60	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Dusin Comment (Nato 7) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	5.3 4.4	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	16.7 14	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	35	Α		
Maximum Continuous Body Diode Forward Current (	Is	2.3	Α		
Avalanche Current (Note 8) L = 10mH	I <sub>AS</sub>	3.5	Α		
Avalanche Energy (Note 8) L = 10mH	E <sub>AS</sub>	65	mJ		

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 6)		$P_{D}$	1.5	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	100	°C/W	
Internal nesistance, Junction to Ambient (Note 6)	t<10s		61	C/VV	
Total Power Dissipation (Note 7)		$P_D$	2.1	W	
Thermal Resistance, Junction to Ambient (Note 7)  Steady Str t<10s		$R_{ heta JA}$	72	°C/W	
			44		
Thermal Resistance, Junction to Case (Note 7)		Rejc	7.25		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C	

### Electrical Characteristics (@TA= +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage		60			V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C		_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D		34	50		$V_{GS} = 10V, I_D = 5.1A$	
Static Drain-Source On-nesistance	R <sub>DS(ON)</sub>	_	45	65	mΩ	$V_{GS} = 4.5V, I_D = 4.4A$	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	CISS	1	584	-	pF	25// 20/	
Output Capacitance	Coss		83		pF	$V_{DS} = 25V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	24	_	pF	71 = 1.UIVIDZ	
Gate Resistance	R <sub>G</sub>		3.8		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	4.2	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	_	8.8	_	nC	\	
Gate-Source Charge	Q <sub>GS</sub>	_	1.8	_	nC	$V_{DS} = 44V, I_{D} = 5.2A$	
Gate-Drain Charge	$Q_{GD}$	_	1.8	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>		3.4	_	ns		
Turn-On Rise Time	t <sub>R</sub>		1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 1A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.1	_	ns		
Turn-Off Fall Time	t <sub>F</sub>		4.5	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	12.9	_	ns	1 2 6 A di/dt 100 A /	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		5.4	_	nC	$I_F = 2.6A$ , di/dt = 100A/ $\mu$ s	

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

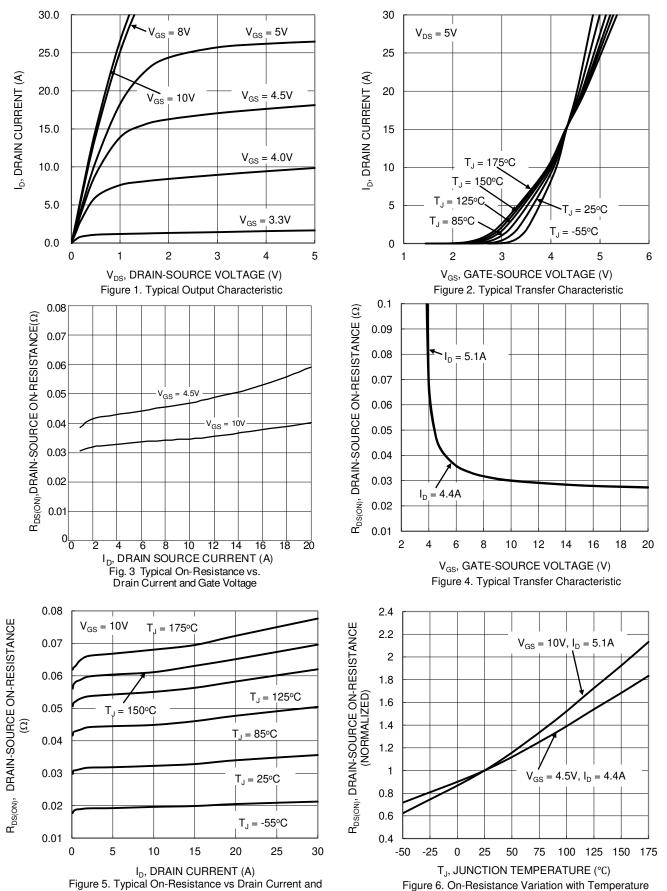
<sup>7.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

<sup>8.</sup>  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_{J}$  = +25°C.

<sup>9.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.





Temperature



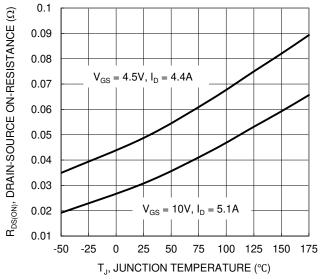
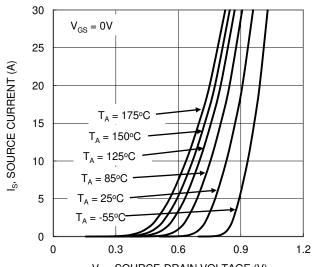


Figure 7. On-Resistance Variation with Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

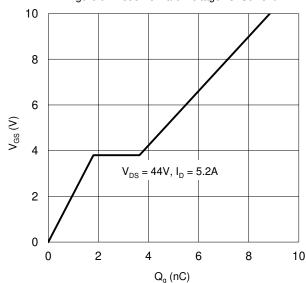


Figure 11. Gate Charge

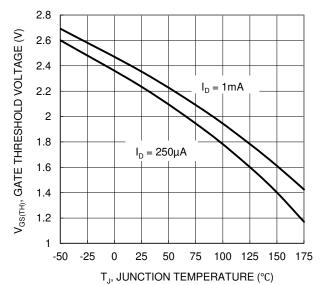


Figure 8. Gate Threshold Variation vs Junction Temperature

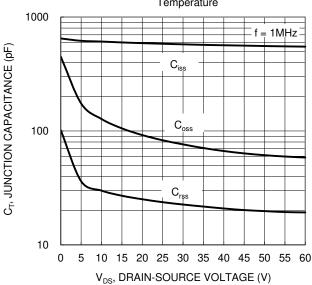


Figure 10. Typical Junction Capacitance

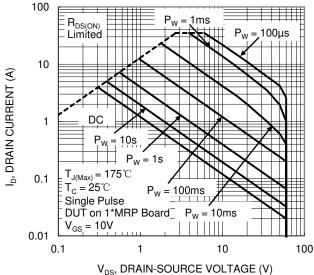


Figure 12. SOA, Safe Operation Area



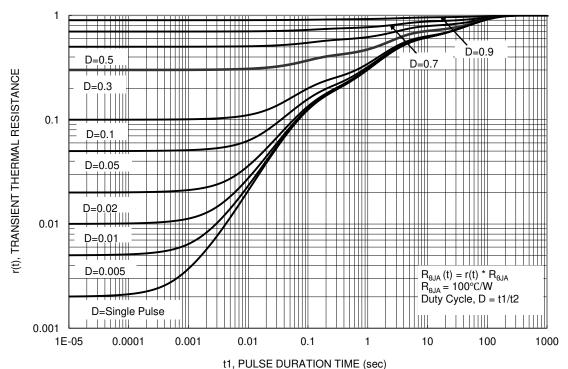


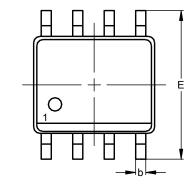
Figure 13. Transient Thermal Resistance

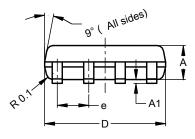


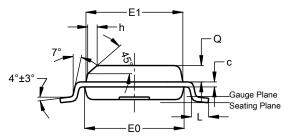
## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SO-8** 





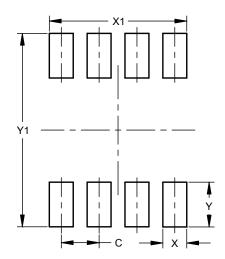


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
<b>A</b> 1	0.10	0.20	0.15		
q	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
e – 1.2					
h	-	_	0.35		
Г	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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